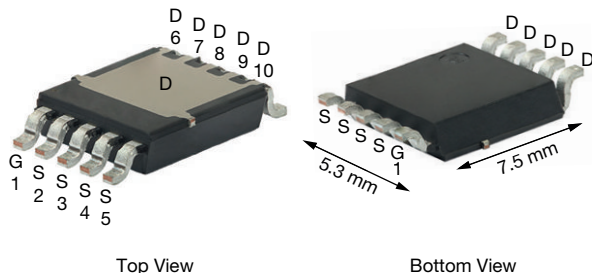


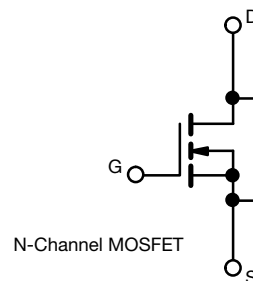
Automotive N-Channel 100 V (D-S) 175 °C MOSFET

PowerPAK® SO-10LR


FEATURES

- TrenchFET® Gen V power MOSFET
- AEC-Q101 qualified
- 100 % R_g and UIS tested
- Q_{gd}/Q_{gs} ratio < 1 optimizes switching characteristics
- Material categorization:
for definitions of compliance please see www.vishay.com/doc?99912

AUTOMOTIVE
GRADE

RoHS
COMPLIANT
HALOGEN
FREE


N-Channel MOSFET

PRODUCT SUMMARY

V_{DS} (V)	100
$R_{DS(on)}$ (Ω) at $V_{GS} = 10$ V	0.0370
I_D (A) ^d	200
Configuration	Single

ORDERING INFORMATION

Package	PowerPAK SO-10LR
Lead (Pb)-free and halogen-free	SQJ510ER (for detailed order number please see www.vishay.com/doc?79776)

ABSOLUTE MAXIMUM RATINGS ($T_C = 25$ °C, unless otherwise noted)

PARAMETER	SYMBOL	LIMIT	UNIT
Drain-source voltage	V_{DS}	100	V
Gate-source voltage	V_{GS}	± 20	
Continuous drain current ^d	I_D	200	A
		115	
Continuous source current (diode conduction) ^d	I_S	290	
Pulsed drain current ^d	I_{DM}	350	
Single pulse avalanche current	I_{AS}	50	
Single pulse avalanche energy	E_{AS}	125	mJ
Maximum power dissipation	P_D	319	W
		106	
Operating junction and storage temperature range	T_J, T_{stg}	-55 to +175	°C
Soldering recommendations (peak temperature) ^b		260	

THERMAL RESISTANCE RATINGS

PARAMETER	SYMBOL	LIMIT	UNIT
Junction-to-ambient ^c	R_{thJA}	42	°C/W
Junction-to-case (drain)	R_{thJC}	0.5	

Notes

- When mounted on 1" square PCB (FR4 material)
- See solder profile (www.vishay.com/doc?73257). The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection
- Using thermal characterization methods based on JESD51-14
- Values based on R_{thJC} and T_C of 25 °C. Actual values achievable will be dependent on the thermal characteristics of the complete system



SPECIFICATIONS (T _C = 25 °C, unless otherwise noted)							
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT
Static							
Drain-source breakdown voltage	V _{DS}	V _{GS} = 0, I _D = 250 μA		100	-	-	V
Gate-source threshold voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = 250 μA		2.0	3.0	4.0	
Gate-source leakage	I _{GSS}	V _{DS} = 0 V, V _{GS} = ± 20 V		-	-	± 100	nA
Zero gate voltage drain current	I _{DSS}	V _{GS} = 0 V	V _{DS} = 100 V	-	-	1	μA
		V _{GS} = 0 V	V _{DS} = 100 V, T _J = 125 °C	-	-	50	
		V _{GS} = 0 V	V _{DS} = 100 V, T _J = 175 °C	-	-	500	
On-state drain current ^a	I _{D(on)}	V _{GS} = 10 V	V _{DS} ≥ 5 V	20	-	-	A
Drain-source on-state resistance ^a	R _{DS(on)}	V _{GS} = 10 V	I _D = 10 A	-	0.00295	0.00370	Ω
		V _{GS} = 10 V	I _D = 10 A, T _J = 125 °C	-	-	0.00657	
		V _{GS} = 10 V	I _D = 10 A, T _J = 175 °C	-	-	0.00830	
Forward transconductance ^b	g _{fs}	V _{DS} = 15 V, I _D = 10 A		-	83	-	S
Dynamic ^b							
Input capacitance	C _{iss}	V _{GS} = 0 V	V _{DS} = 50 V, f = 1 MHz	-	3903	5860	pF
Output capacitance	C _{oss}			-	987	1485	
Reverse transfer capacitance	C _{rss}			-	8	16	
Total gate charge ^c	Q _g	V _{GS} = 10 V	V _{DS} = 50 V, I _D = 20 A	-	45	68	nC
Gate-source charge ^c	Q _{gs}			-	19.4	-	
Gate-drain charge ^c	Q _{gd}			-	1.8	-	
Gate resistance	R _g	f = 1 MHz		0.7	1.43	2.2	Ω
Turn-on delay time ^c	t _{d(on)}	V _{DD} = 50 V, R _L = 2.5 Ω I _D ≅ 20 A, V _{GEN} = 10 V, R _g = 1 Ω		-	18	36	ns
Rise time ^c	t _r			-	8	16	
Turn-off delay time ^c	t _{d(off)}			-	29	60	
Fall time ^c	t _f			-	7	15	
Source-Drain Diode Ratings and Characteristics ^b							
Pulsed current ^a	I _{SM}			-	-	350	A
Forward voltage	V _{SD}	I _F = 10 A, V _{GS} = 0 V		-	0.76	1.1	V
Body diode reverse recovery time	t _{rr}	I _F = 10 A, di/dt = 100 A/μs		-	70	140	ns
Body diode reverse recovery charge	Q _{rr}			-	143	290	nC
Reverse recovery fall time	t _a			-	42	-	ns
Reverse recovery rise time	t _b			-	28	-	
Body diode peak reverse recovery current	I _{RM(REC)}			-	-3.4	-	A

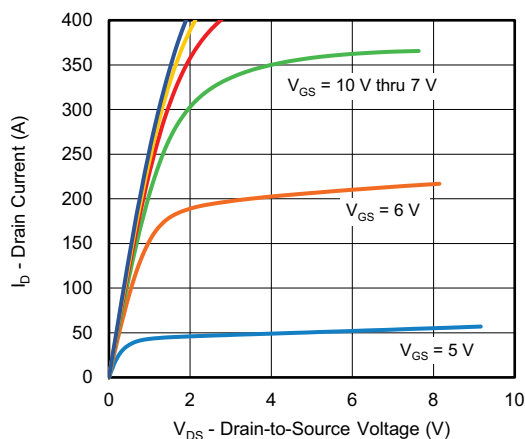
Notes

- e. Pulse test; pulse width ≤ 300 μs, duty cycle ≤ 2 %
 f. Guaranteed by design, not subject to production testing
 g. Independent of operating temperature

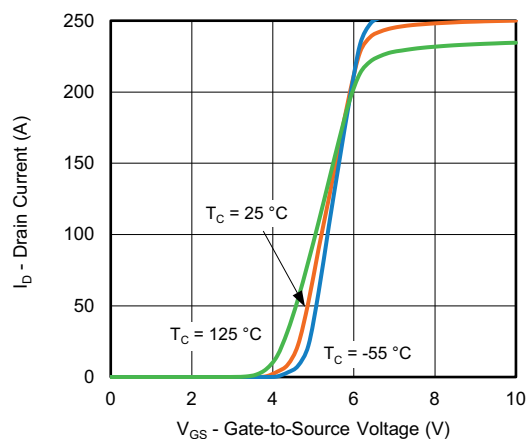
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



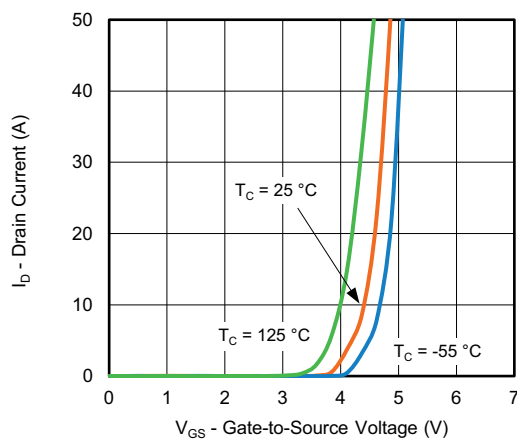
TYPICAL CHARACTERISTICS ($T_A = 25\text{ }^{\circ}\text{C}$, unless otherwise noted)



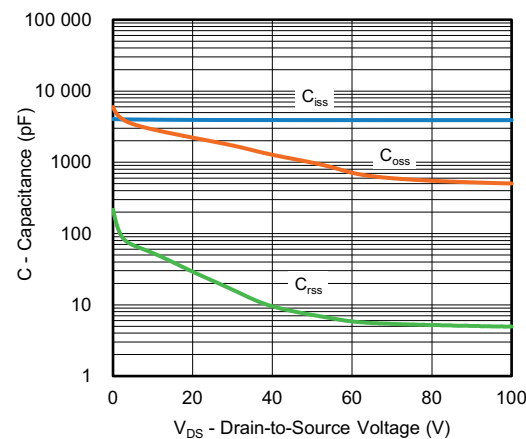
Output Characteristics



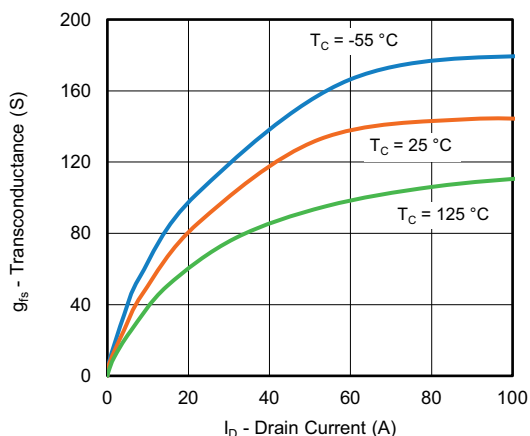
Transfer Characteristics



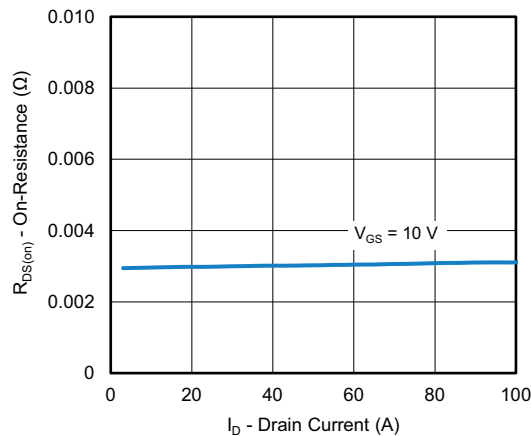
Transfer Characteristics



Capacitance



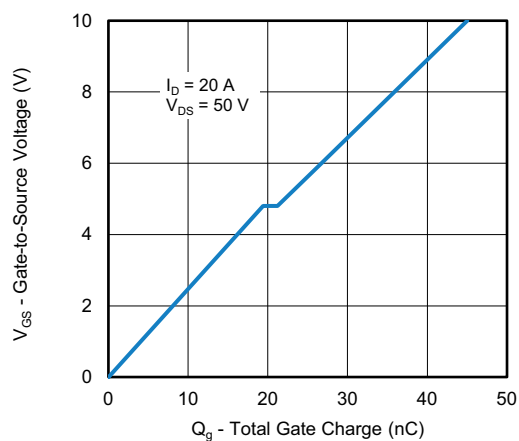
Transconductance



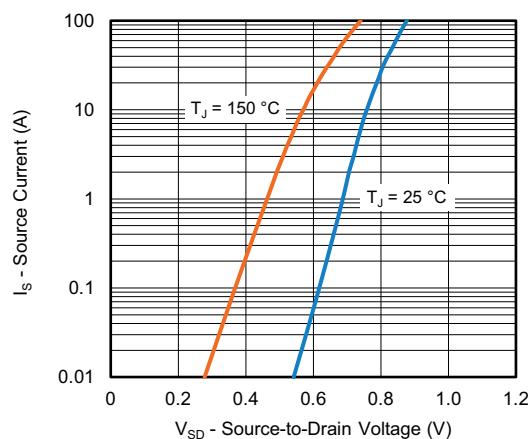
On-Resistance vs. Drain Current



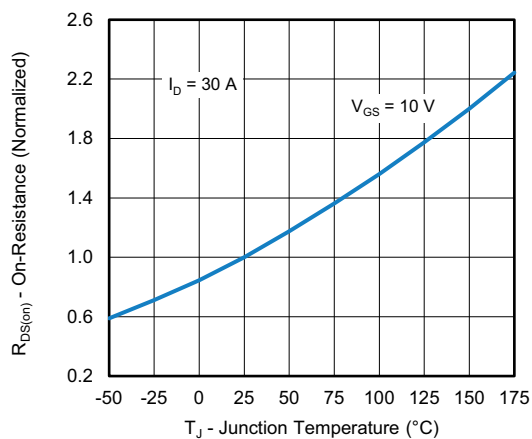
TYPICAL CHARACTERISTICS ($T_A = 25\text{ }^{\circ}\text{C}$, unless otherwise noted)



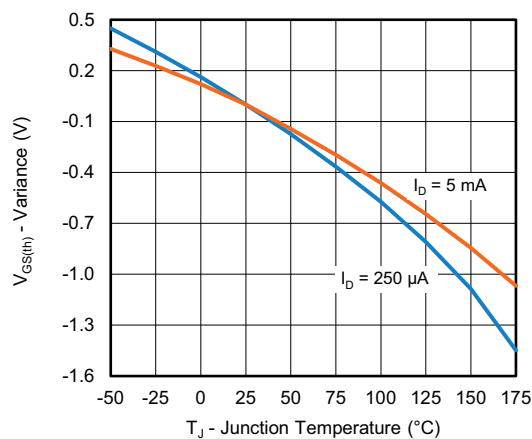
Gate Charge



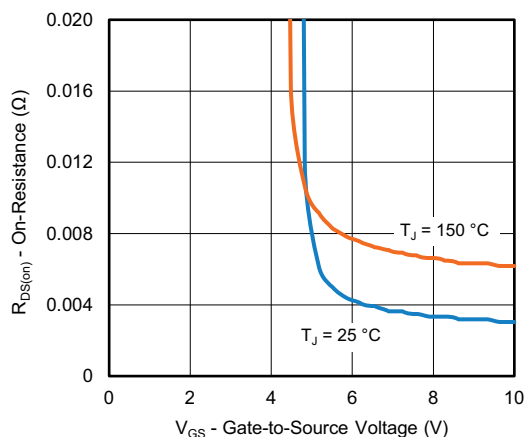
Source Drain Diode Forward Voltage



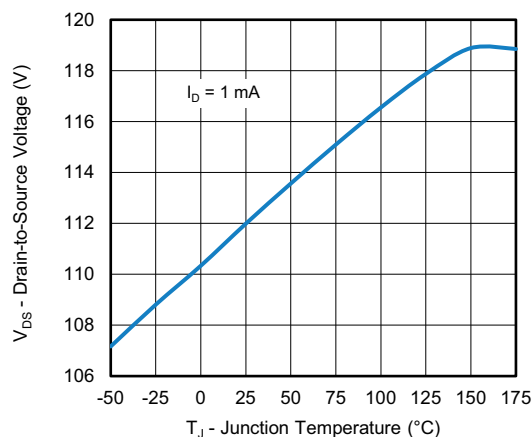
On-Resistance vs. Junction Temperature



Threshold Voltage



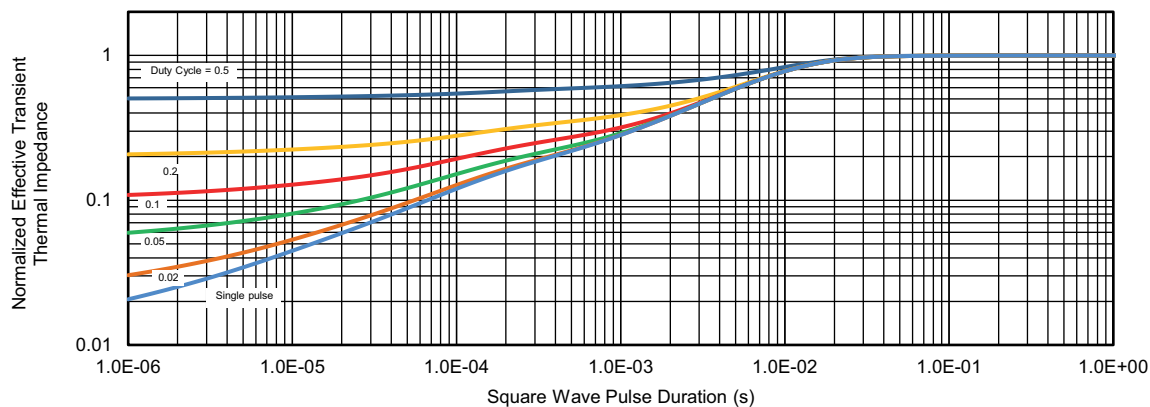
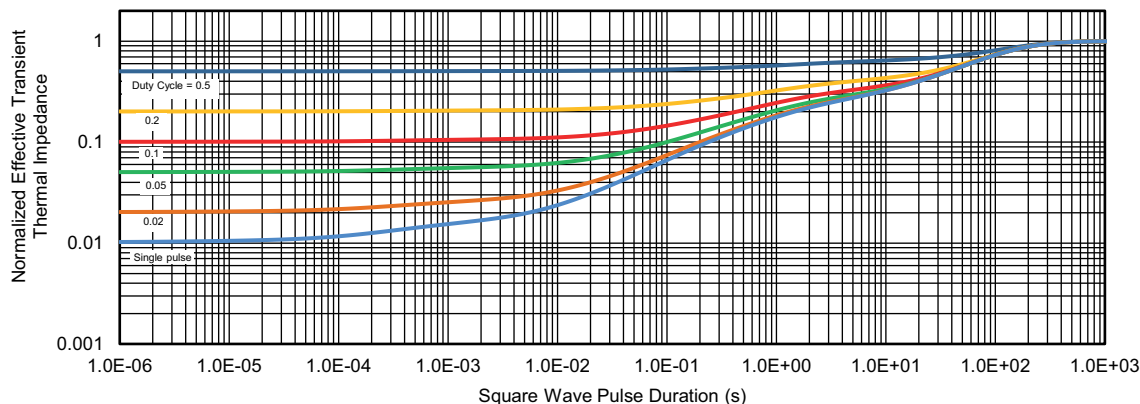
On-Resistance vs. Gate-to Source Voltage



Drain Source Breakdown vs. Junction Temperature

Note

a. $V_{GS} >$ minimum V_{GS} at which $R_{DS(on)}$ is specified

TYPICAL CHARACTERISTICS ($T_A = 25\text{ }^{\circ}\text{C}$, unless otherwise noted)

Normalized Thermal Transient Impedance, Junction-to-Case

Normalized Thermal Transient Impedance, Junction-to-Ambient
Note

- The characteristics shown in the two graphs
 - Normalized Transient Thermal Impedance Junction-to-Ambient ($25\text{ }^{\circ}\text{C}$)
 - Normalized Transient Thermal Impedance Junction-to-Case ($25\text{ }^{\circ}\text{C}$)
 are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions

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